



DISCRETE POWER AND SIGNAL TECHNOLOGIES

ULTRA FAST DIODE

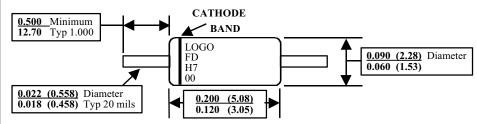
Information Only Data Sheet

FINAL REVERSE CURRENT & FORWARD VOLTAGE LIMITS MIGHT BE INCREASED SLIGHTLY

Absolute Maximum Ratings (note 1) TA = 25°C unless otherwise noted

Parameter	Value	Units
Storage Temperature	-65 to +200	°C
Maximum Junction Temperature	-65 to +175	OO
Total Power Dissipation at 25 ⁰ C	250	mW
Derate above 25 ^o C	1.67	mW/ ^o C
Working Inverse Voltage	20	V
DC Forward Current	150	mA

Note 1: These ratings are limiting values above which the serviceability of any semiconductor device may be impaired



Electrical Characteristics TA = 25°C unless otherwise noted

SYM	CHARACTERISTICS	MIN	MAX	UNITS	TEST CONDITIONS
B_V	Breakdown Voltage	30		V	I _R = 5.0 uA
I _R	Reverse Leakage		50 50	nA uA	$V_{R} = 20 V$ $V_{R} = 20 V T_{A} = 150^{\circ}C$
V _F	Forward Voltage	420 520 640 760 810 0.89	500 610 740 900 990 1.25	mV mV mV mV V	$\begin{array}{rcl} I_{\rm F} &=& 10 \ {\rm uA} \\ I_{\rm F} &=& 100 \ {\rm uA} \\ I_{\rm F} &=& 1.0 \ {\rm mA} \\ I_{\rm F} &=& 10 \ {\rm mA} \\ I_{\rm F} &=& 20 \ {\rm mA} \\ I_{\rm F} &=& 50 \ {\rm mA} \end{array}$
T _{RR}	Reverse Recovery Time		900	ps	I _F = I _R = 10 mA I _{RR} = 1.0 mA R _{Loop} = 100 Ohm
C _T	Diode Capacitance		1.5	pF	V _R = 0 V, f = 1.0 MHz

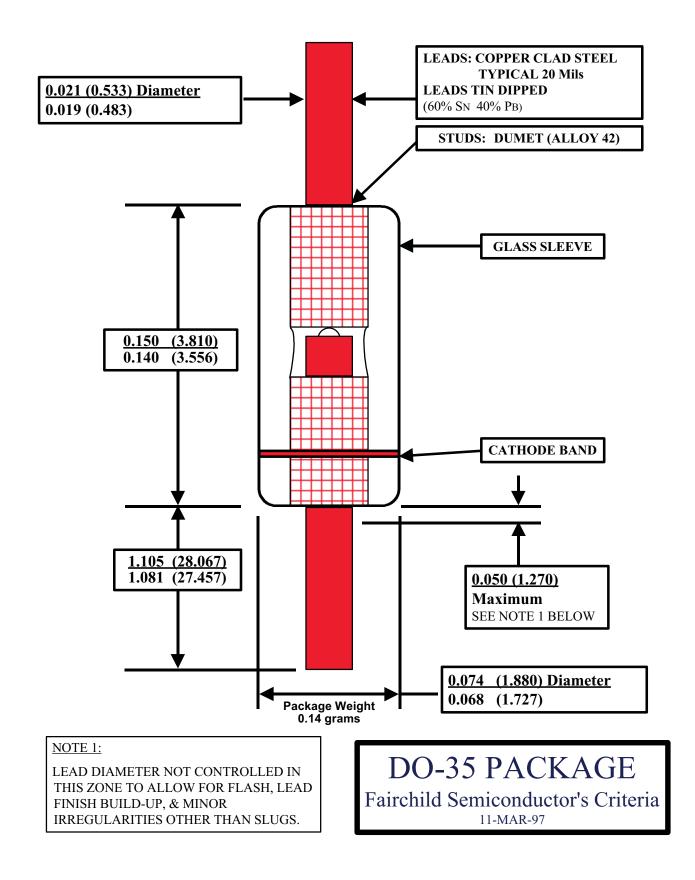


DISCRETE POWER AND SIGNAL TECHNOLOGIES

SEMICONDUCTOR TM

STANDARD DIGITAL MARKING CRITERIA

MAXIMUM CHARACTERS PER LINE: 3 MAXIMUM NUMBER OF LINES: 4 LOGO AND CHARACTERS M & W COUNT AS 2 CHARACTERS EACH





DISCRETE POWER AND SIGNAL TECHNOLOGIES

FD700

Ultra Fast Diode Diode

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Storage Temperature	-65 to +200	°C
Maximum Junction Temperature	-65 to +175	OO
Total Power Dissipation at 25 ^o C	250	mW
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Working Inverse Voltage	20	V
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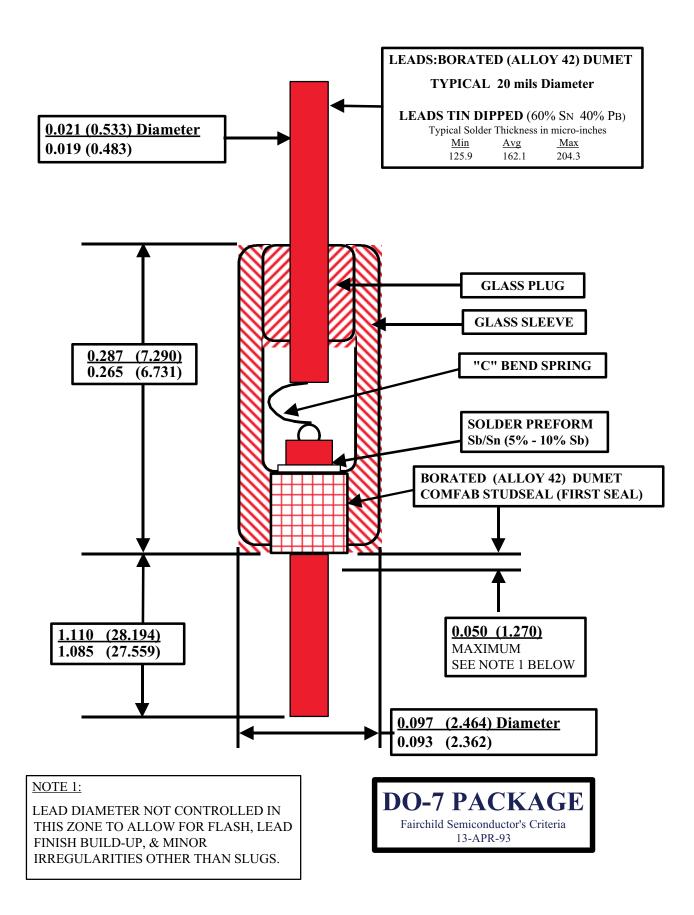


Electrical Characteristics TA = 25^oC unless otherwise noted

SYM	CHARACTERISTICS	MIN	МАХ	UNITS	TEST CONDITIONS
B _V	Breakdown Voltage	30		V	I _R = 5.0 uA
I _R	Reverse Leakage		50 50	nA uA	$V_{R} = 20 V$ $V_{R} = 20 V T_{A} = 150^{\circ}C$
V _F	Forward Voltage	420 520 640 760 810 0.89	500 610 740 880 950 1.10	mV mV mV mV V	$\begin{array}{rcl} I_{\rm F} &=& 10 \ {\rm uA} \\ I_{\rm F} &=& 100 \ {\rm uA} \\ I_{\rm F} &=& 1.0 \ {\rm mA} \\ I_{\rm F} &=& 10 \ {\rm mA} \\ I_{\rm F} &=& 20 \ {\rm mA} \\ I_{\rm F} &=& 50 \ {\rm mA} \end{array}$
T _{RR}	Reverse Recovery Time		700	ps	I _F = I _R = 10 mA I _{RR} = 1.0 mA R _{Loop} = 100 Ohm
C _T	Diode Capacitance		1.0	pF	V _R = 0 V, f = 1.0 MHz







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	First Production

Rev. H3